

### **Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

### **Listing of Claims:**

Claim 1 (canceled)

Claim 2 (canceled)

Claim 3 (canceled)

Claim 4 (canceled)

Claim 5 (previously presented): A bipolar junction transistor, comprising:

a buried collector layer;

a counterdoped collector region adjacent to said buried collector layer wherein said collector region contains at least  $0.5 \times 10^{17} \text{cm}^{-3}$  scattering centers;

a base region adjacent to said counterdoped collector region; and

an emitter region adjacent to said base region.

Claim 6 (original): The bipolar junction transistor of claim 5 wherein said scattering centers are a species selected from the group consisting of boron, aluminum, gallium, indium, carbon, phosphorous, arsenic and antimony.

Claim 7 (previously presented): The bipolar junction transistor of claim 5 wherein the distance from the edge of said buried collector layer which is adjacent to said counterdoped collector region to the edge of said base region which is adjacent to said collector region is less than 1500 angstroms.

Claim 8 (original): The bipolar junction transistor of claim 5 wherein the base region is silicon germanium.

Claim 9 (previously presented): The bipolar junction transistor of claim 5 wherein the scattering centers of said counterdoped collector region are neutral scattering centers.